4N22, 4N23, 4N24 [A] (TX, TXV) 4N47, 4N48, 4N49 [A] (TX, TXV)

#### Features:

- TO-78 hermetically sealed package
- High current transfer ratio
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- TX and TXV devices processed to MIL-PRF-19500

#### **Description:**

Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed TO-78 package. Devices are designed for military and/or harsh environments. The suffix letter "A" denotes the collector is electrically isolated from the case.

*The 4N22, 4N22A, 4N23, 4N23A,4N24, and 4N24A (TX, TXV) devices are processed to MIL-PRF-19500/486. The 4N47, 4N47A, 4N48, 4N48A, 4N49, and 4N49A (TX, TXV) devices are processed to MIL-PRF-19500/548.* 

Please contact your local representative or OPTEK for more information.

#### **Applications:**

- High-voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment

	ORDERING INF	ORMATION			
Part Number	Isolation Voltage (kV)	CTR % Min / Max	I <sub>F</sub> (mA) Typ / Max	V <sub>CE</sub> (Volts) Max	Processing MIL-PRF- 195000
4N22 or 4N22A					
4N22TX or 4N22ATX		25 / NA	10/40	35	486
4N22TXV or 4N22ATXV					
4N23 or 4N23A		20 / NA			
4N23TX or 4N23ATX					
4N23TXV or 4N23ATXV					
4N24 or 4N24A		40 / NA			
4N24TX or 4N24ATX					
4N24TXV or 4N24ATXV					
4N47 or 4N47A	1	50 / NA			
4N47TX or 4N47ATX					
4N47TXV or 4N47ATXV					
4N48 or 4N48A		100 / 500			
4N48TX or 4N48ATX					
4N48TXV or 4N48ATXV					
4N49 or 4N49A		200 /			
4N49TX or 4N49ATX					
4N49TXV or 4N49ATXV		1,000			

General Note

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4N22, 4N23, 4N24 [A] (TX, TXV) 4N47, 4N48, 4N49 [A] (TX, TXV)

Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)	
Storage Temperature Range 4N22, 4N22A, 4N23, 4N23A, 4N24, 4N24A (TX, TXV) 4N47, 4N47A, 4N48, 4N48A, 4N49, 4N49A (TX, TXV)	-65° C to +125°
Operating Temperature Range 4N22, 4N22A, 4N23, 4N23A, 4N24, 4N24A (TX, TXV) 4N47, 4N47A, 4N48, 4N48A, 4N49, 4N49A (TX, TXV)	-55° C to +125°
Input-to-Output Isolation Voltage	± 1.00 kVDC <sup>(</sup>
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(</sup>
Input Diode	
Forward DC Current (65° C or below)	40 m.
Reverse Voltage	2
Peak Forward Current (1 μs pulse width, 300 pps) 4N22, 4N22A, 4N23, 4N23A, 4N24, 4N24A (TX, TXV)	1
Power Dissipation	60 mW <sup>(</sup>
Output Phototransistor (4N22, 4N22A, 4N23, 4N23A, 4N24, 4N24A )	
Continuous Collector Current	50 m
Collector-Emitter Voltage	35
Collector-Base Voltage	35
Emitter-Base Voltage	4
Power Dissipation	300 mW <sup>(</sup>
Output Phototransistor (4N47, 4N47A, 4N48, 4N48A, 4N49, 4N49A )	1
Continuous Collector Current	50 m
Collector-Emitter Voltage	40
Collector-Base Voltage	45
Emitter-Base Voltage	7.0
Power Dissipation	300 mW

Notes:

1. Measured with input leads shorted together and output leads shorted together.

2. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

3. Derate linearly 1.0 mW/° C above 65° C.

4. Derate linearly 3.0 mW/° C above 25° C.

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4N22, 4N23, 4N24 [A] (TX, TXV) 4N47, 4N48, 4N49 [A] (TX, TXV)



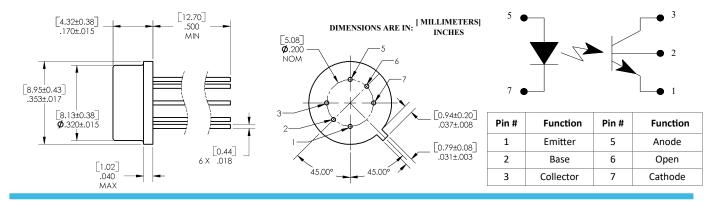
### Performance

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS
nput Diode						,
	Forward Voltage					
	4N22, 4N23, 4N24 [A] (TX, TXV)	0.80	-	1.30		I <sub>F</sub> = 10.0 mA
	4N22, 4N23, 4N24 [A] (TX, TXV)	1.00	-	1.50		$I_{\rm F}$ = 10.0 mA, $T_{\rm A}$ = -55° C <sup>(1)</sup>
VF	4N22, 4N23, 4N24 [A] (TX, TXV)	0.70	-	1.20	V	$I_F = 10.0 \text{ mA}, T_A = -100^{\circ} \text{ C}^{(1)}$
	4N47, 4N48, 4N49 [A] (TX, TXV)	0.80	-	1.50		I <sub>F</sub> = 10.0 mA
	4N47, 4N48, 4N49 [A] (TX, TXV)	1.00	-	1.70		$I_{\rm F}$ = 10.0 mA, $T_{\rm A}$ = -55° C <sup>(1)</sup>
	4N47, 4N48, 4N49 [A] (TX, TXV)	0.70	-	1.30		$I_F = 10.0 \text{ mA}, T_A = -100^{\circ} \text{ C}^{(1)}$
I <sub>R</sub>	Reverse Current	-	-	100	μA	V <sub>R</sub> = 2.0 V
utput Pho	totransistor	1				1
	Collector-Emitter Breakdown Voltage					
V <sub>(BR)CEO</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	35	-	-	v	$I_{c} = 1.0 \text{ mA}, I_{B} = 0, I_{F} = 0$
(54)620	4N47, 4N48, 4N49 [A] (TX, TXV)	40	-	-		$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0, I_{\rm F} = 0$
	Collector-Base Breakdown Voltage					
V <sub>(BR)CBO</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	35	-	-	V	$I_{C} = 100 \ \mu A$ , $I_{B} = 0$ , $I_{F} = 0$
. ,	4N47, 4N48, 4N49 [A] (TX, TXV)	45	-	-		$I_{C} = 100 \ \mu A$ , $I_{B} = 0$ , $I_{F} = 0$
	Emitter-Base Breakdown Voltage					
V <sub>(BR)EBO</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	4	-	-	V	I <sub>E</sub> = 100 μA, I <sub>C</sub> = 0, I <sub>F</sub> = 0
	4N47, 4N48, 4N49 [A] (TX, TXV)	7	-	-		$I_{E}$ = 100 $\mu A,$ $I_{C}$ = 0, $I_{F}$ = 0
	Collector-Emitter Dark Current					
ICEO	4N22, 4N23, 4N24 [A] (TX, TXV)	-	-	100	nA	$V_{CE} = 20 V, I_B = 0, I_F = 0$
	4N47, 4N48, 4N49 [A] (TX, TXV)	-	-	100	μA	$V_{CE} = 20 \text{ V}, I_{B} = 0, I_{F} = 0, T_{A} = 100^{\circ} \text{ C}^{(2)}$
	Collector-Emitter Dark Current					
I <sub>C(OFF)</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	-	-	100	nA	$V_{CE} = 20 V, I_B = 0, I_F = 0$
	4N47, 4N48, 4N49 [A] (TX, TXV)	-	-	100	μΑ	$V_{CE} = 20 \text{ V}, \text{ I}_{B} = 0, \text{ I}_{F} = 0, \text{ T}_{A} = 100^{\circ} \text{ C}^{(1)}$
	Collector-Base Dark Current					
I <sub>CB(OFF)</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	-	-	10	nA	$V_{CB} = 20 V, I_F = 0, I_F = 0$
	4N47, 4N48, 4N49 [A] (TX, TXV)	-	-	10	nA	UB 20 V, IE- 0, IF- 0

Notes:

1. Guaranteed but not tested.

2. Sample tested, LTPD = 10.



General Note

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**Electronics** 

4N22, 4N23, 4N24 [A] (TX, TXV) 4N47, 4N48, 4N49 [A] (TX, TXV)

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS
oupled						
	On-State Collector Current					
	4N22, 4N22A (TX, TXV)	0.15	-	-		$I_{\rm F} = 2.0 \text{ mA}$ , $V_{\rm CF} = 5 \text{ V}$ , $I_{\rm B} = 0$
	4N22, 4N22A (TX, TXV)	2.50	-	-		$I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$
	4N22, 4N22A (TX, TXV)	1.00	-	-		$I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$ , $T_A = -55^{\circ} \text{ C}^{(1)}$
	4N22, 4N22A (TX, TXV)	1.00	-	-		$I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$ , $T_A = -35 \text{ C}$ $I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$ , $T_A = 100^{\circ} \text{ C}^{(1)}$
	4N23, 4N23A (TX, TXV)	0.20	-	-		I <sub>F</sub> = 2.0 mA , V <sub>CE</sub> = 5 V, I <sub>B</sub> = 0
	4N23, 4N23A (TX, TXV)	6.00	-	_		$I_{\rm F} = 10.0 \text{ mA}$ , $V_{\rm CF} = 5 \text{ V}$ , $I_{\rm B} = 0$
	4N23, 4N23A (TX, TXV)	2.50	-	-		$I_F = 10.0 \text{ mA}$ , $V_{CF} = 5 \text{ V}$ , $I_B = 0$ , $T_A = -55^{\circ} \text{ C}^{(1)}$
	4N23, 4N23A (TX, TXV)	2.50	-	-		$I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$ , $T_A = 100^{\circ} \text{ C}^{(1)}$
I <sub>C(ON)</sub>	4N24, 4N24A (TX, TXV)	0.40	-	-		$I_{\rm F} = 2.0 \text{ mA}$ , $V_{\rm CE} = 5 \text{ V}$ , $I_{\rm B} = 0$
	4N24, 4N24A (TX, TXV)	10.0	-	-		$I_F = 10.0 \text{ mA}$ , $V_{CF} = 5 \text{ V}$ , $I_B = 0$
	4N24, 4N24A (TX, TXV)	4.00	-	_	mA	$I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$ , $T_A = -55^{\circ} \text{ C}^{(1)}$
	4N24, 4N24A (TX, TXV)			$I_F = 10.0 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $I_B = 0$ , $T_A = 100^{\circ} \text{ C}^{(1)}$		
	4N47, 4N47A (TX, TXV)	0.50	-	-		$I_F = 1.0 \text{ Ma}, V_{CF} = 5.0 \text{ V}, I_B = 0$
	4N47, 4N47A (TX, TXV)	0.70	-	-		$I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$
	4N47, 4N47A (TX, TXV)	0.50	-	-		$I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)}$
	4N48, 4N48A (TX, TXV)	1.00	-	5		$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0$
	4N48, 4N48A (TX, TXV)	1.40	-	-		$I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$
	4N48, 4N48A (TX, TXV)	1.00	-	-		$I_F$ = 2.0 mA, $V_{CE}$ = 5.0 V, $I_B$ = 0, $T_A$ = 100° $C^{(1)}$
	4N49, 4N49A (TX, TXV)	2.00	-	10		$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0$
	4N49, 4N49A (TX, TXV)	2.80	-	-		$I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$
	4N49, 4N49A (TX, TXV)	2.00	-	-		$I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)}$
I <sub>CB(ON)</sub>	On-State Collector Base	20			μA	
cb(ch)	4N47, 4N48, 4N49 [A] (TX, TXV)	30	-	-	•	$V_{CB} = 5 V, I_E = 0, I_F = 10 mA$
	Collector-Emitter Saturation Voltage				v	I <sub>F</sub> = 20 mA , I <sub>C</sub> = 2.5 mA, I <sub>B</sub> = 0
	4N22, 4N23, 4N24 [A] (TX, TXV)	-	-	0.30		
	4N22, 4N23, 4N24 [A] (TX, TXV)	-	-	0.30		$I_F = 20 \text{ mA}$ , $I_C = 5.0 \text{ mA}$ , $I_B = 0$
V <sub>CE(SAT)</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	-	-	0.30		$I_F = 20 \text{ mA}$ , $I_C = 10.0 \text{ mA}$ , $I_B = 0$
	4N47, 4N47A (TX, TXV)	-	-	0.30		$I_F = 2.0 \text{ mA}, I_C = 0.5 \text{ mA}, I_B = 0$
	4N48, 4N48A (TX, TXV) 4N49, 4N49A (TX, TXV)	-	-	0.30 0.30		$I_F = 2.0 \text{ mA}, I_C = 1.0 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 2.0 \text{ mA}, I_B = 0$
	DC Current Gain					
H <sub>FE</sub>	4N22, 4N22A (TX, TXV)		-	_		
	4N23, 4N23A (TX, TXV)		-	-	v	
	4N24, 4N24A (TX, TXV)	>300	-	-		$V_{CE}$ = 5.0 V , $I_C$ = 10.0 mA, $I_F$ = 0 mA
	4N47, 4N48, 4N49 [A] (TX, TXV)		-	-		
	Resistance (Input-to-Output)	44				
R <sub>IO</sub>	4N22, 4N23, 4N24 [A] (TX, TXV)	10 <sup>11</sup>	-	-	Ω	$V_{I-0} = \pm 1000 \text{ VDC}^{(3)}$
	4N47, 4N48, 4N49 [A] (TX, TXV)	10 <sup>11</sup>	-	-		V <sub>I-O</sub> = ± 1000 VDC <sup>(3)</sup>
CIO	Capacitance (Input-to-Output)	-	-	5	pF	V <sub>I-O</sub> = 0 V, f = 1.0 MHz <sup>(3)</sup>

General Note

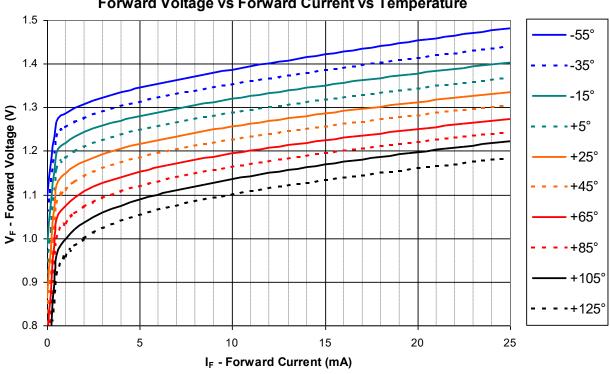
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4N22, 4N23, 4N24 [A] (TX, TXV) 4N47, 4N48, 4N49 [A] (TX, TXV)

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS
Coupled						
	Output Rise Time					
	4N22A (TX, TXV)	-	-	15	μs	$V_{CC}$ = 10.0 V , $I_{F}$ = 10.0 mA, $R_{L}$ = 100 mA
T <sub>R</sub>	4N23A (TX, TXV)	-	-	15		$V_{\text{CC}}$ = 10.0 V , $I_{\text{F}}$ = 10.0 mA, $R_{\text{L}}$ = 100 mA
	4N24A (TX, TXV)	-	-	20		$V_{CC}$ = 10.0 V , I <sub>F</sub> = 10.0 mA, R <sub>L</sub> = 100 mA
	4N47 (TX. TXV)	-	-	20		$V_{CC}$ = 10.0 V , $I_F$ = 5.0 mA, $R_L$ = 100 $\Omega$
	4N48 (TX. TXV)	-	-	20		$V_{CC} = 10.0 \text{ V}$ , $I_{F} = 5.0 \text{ mA}$ , $R_{L} = 100 \Omega$
	4N49 (TX. TXV)	-	-	25		$V_{CC} = 10.0 \text{ V}$ , $I_F = 5.0 \text{ mA}$ , $R_L = 100 \Omega$
	Output Fall Time					
	4N22A (TX, TXV)	-	-	15	μs	$V_{CC}$ = 10.0 V , $I_F$ = 10.0 mA, $R_L$ = 100 $\Omega$
T <sub>F</sub>	4N23A (TX, TXV)	-	-	15		$V_{CC}$ = 10.0 V , $I_F$ = 10.0 mA, $R_L$ = 100 $\Omega$
	4N24A (TX, TXV)	-	-	20		$V_{CC}$ = 10.0 V , $I_F$ = 10.0 mA, $R_L$ = 100 $\Omega$
	4N47 (TX. TXV)	-	-	20		$V_{CC}$ = 10.0 V , $I_F$ = 5.0 mA, $R_L$ = 100 $\Omega$
	4N48 (TX. TXV)	-	-	20		$V_{CC}$ = 10.0 V , $I_F$ = 5.0 mA, $R_L$ = 100 $\Omega$
	4N49 (TX. TXV)	-	-	25		$V_{CC} = 10.0 \text{ V}$ , $I_F = 5.0 \text{ mA}$ , $R_L = 100 \Omega$

#### **Typical Performance Curves**



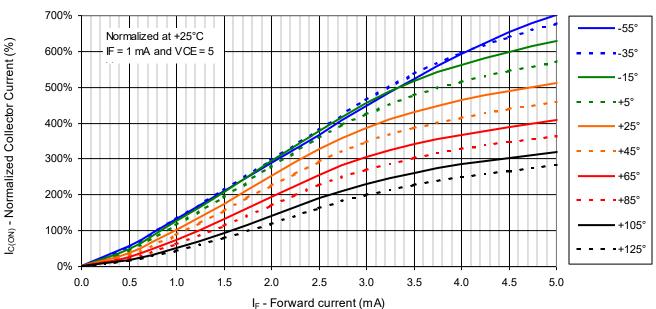
#### Forward Voltage vs Forward Current vs Temperature

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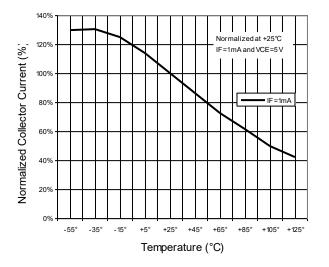
4N22, 4N23, 4N24 [A] (TX, TXV) 4N47, 4N48, 4N49 [A] (TX, TXV)

#### **Typical Performance Curves**



#### **Collector Current vs Forward Current vs Temperature**

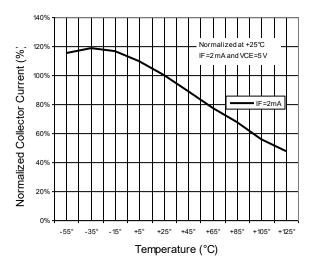
Normalized Collector Current Vs Temperature



Normalized Collector Current Vs Temperature

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